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The third column is the impact factor (IF) of the journal, and the fourth column is the number of citations of the article.

38 papers	921 citations	16 h-index	30 g-index
42 ext. papers	1,197 ext. citations	2.9 avg, IF	4.55 L-index

#	Paper	IF	Citations
38	Enhancement-Mode Ga ₂ O ₃ Vertical Transistors With Breakdown Voltage >1 kV. <i>IEEE Electron Device Letters</i> , 2018 , 39, 869-872	4.4	166
37	Field-Plated Ga ₂ O ₃ Trench Schottky Barrier Diodes With a BV ₂ / $R_{\text{on,sp}}$ of up to 0.95 GW/cm ² . <i>IEEE Electron Device Letters</i> , 2020 , 41, 107-110	4.4	97
36	Breakdown mechanism in 1 kA/cm ² and 960 V E-mode $\text{AlGa}_{2}\text{O}_3$ vertical transistors. <i>Applied Physics Letters</i> , 2018 , 113, 122103	3.4	91
35	1230 V $\text{AlGa}_{2}\text{O}_3$ trench Schottky barrier diodes with an ultra-low leakage current of . <i>Applied Physics Letters</i> , 2018 , 113, 202101	3.4	61
34	. <i>IEEE Transactions on Electron Devices</i> , 2017 , 64, 1635-1641	2.9	58
33	1.1-kV Vertical GaN p-n Diodes With p-GaN Regrown by Molecular Beam Epitaxy. <i>IEEE Electron Device Letters</i> , 2017 , 38, 1071-1074	4.4	50
32	Near-ideal reverse leakage current and practical maximum electric field in $\text{AlGa}_{2}\text{O}_3$ Schottky barrier diodes. <i>Applied Physics Letters</i> , 2020 , 116, 192101	3.4	42
31	Al Gallium oxide power electronics. <i>APL Materials</i> , 2022 , 10, 029201	5.7	33
30	Development of GaN Vertical Trench-MOSFET With MBE Regrown Channel. <i>IEEE Transactions on Electron Devices</i> , 2018 , 65, 2558-2564	2.9	32
29	Fin-channel orientation dependence of forward conduction in kV-class Ga ₂ O ₃ trench Schottky barrier diodes. <i>Applied Physics Express</i> , 2019 , 12, 061007	2.4	29
28	GaN HEMTs on Si With Regrown Contacts and Cutoff/Maximum Oscillation Frequencies of 250/204 GHz. <i>IEEE Electron Device Letters</i> , 2020 , 41, 689-692	4.4	29
27	Guiding Principles for Trench Schottky Barrier Diodes Based on Ultrawide Bandgap Semiconductors: A Case Study in Ga ₂ O ₃ . <i>IEEE Transactions on Electron Devices</i> , 2020 , 67, 3938-3947	2.9	26
26	Activation of buried p-GaN in MOCVD-regrown vertical structures. <i>Applied Physics Letters</i> , 2018 , 113, 062105	3.4	25
25	2019 ,		23
24	2.44 kV Ga ₂ O ₃ vertical trench Schottky barrier diodes with very low reverse leakage current 2018 ,		23
23	1.6 kV Vertical Ga ₂ O ₃ FinFETs With Source-Connected Field Plates and Normally-off Operation 2019 ,		19
22	Thermionic emission or tunneling? The universal transition electric field for ideal Schottky reverse leakage current: A case study in $\text{AlGa}_{2}\text{O}_3$. <i>Applied Physics Letters</i> , 2020 , 117, 222104	3.4	14

21	Realization of GaN PolarMOS using selective-area regrowth by MBE and its breakdown mechanisms. <i>Japanese Journal of Applied Physics</i> , 2019 , 58, SCCD15	1.4	12
20	. <i>IEEE Transactions on Electron Devices</i> , 2020 , 67, 3954-3959	2.9	12
19	600 V GaN vertical V-trench MOSFET with MBE regrown channel 2017 ,		10
18	1.5 kV Vertical Ga ₂ O ₃ Trench-MIS Schottky Barrier Diodes 2018 ,		9
17	. <i>IEEE Transactions on Electron Devices</i> , 2019 , 66, 4597-4603	2.9	8
16	Thermal stability of epitaxial β -Ga ₂ O ₃ and (Al,Ga) ₂ O ₃ layers on m-plane sapphire. <i>Applied Physics Letters</i> , 2021 , 119, 062102	3.4	8
15	2018 ,		7
14	Thermal design of multi-fin Ga ₂ O ₃ vertical transistors. <i>Applied Physics Letters</i> , 2021 , 119, 103502	3.4	6
13	GaN vertical nanowire and fin power MISFETs 2017 ,		5
12	A unified thermionic and thermionic-field emission (TE \square FE) model for ideal Schottky reverse-bias leakage current. <i>Journal of Applied Physics</i> , 2022 , 131, 015702	2.5	5
11	ON-Resistance of Ga ₂ O ₃ Trench-MOS Schottky Barrier Diodes: Role of Sidewall Interface Trapping. <i>IEEE Transactions on Electron Devices</i> , 2021 , 68, 2420-2426	2.9	5
10	Very High Parallel-Plane Surface Electric Field of 4.3 MV/cm in Ga ₂ O ₃ Schottky Barrier Diodes with PtO _x Contacts 2020 ,		4
9	Degradation Mechanisms of GaN-Based Vertical Devices: A Review. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2020 , 217, 1900750	1.6	3
8	Breakdown Mechanisms in β -Ga ₂ O ₃ Trench-MOS Schottky-Barrier Diodes. <i>IEEE Transactions on Electron Devices</i> , 2022 , 69, 75-81	2.9	2
7	Field-plated Ga ₂ O ₃ Trench Schottky Barrier Diodes with a Record High Figure-of-merit of 0.78 GW/cm ² 2019 ,		2
6	Advanced concepts in Ga ₂ O ₃ power and RF devices. <i>Semiconductors and Semimetals</i> , 2021 , 107, 23-47	0.6	2
5	. <i>IEEE Transactions on Electron Devices</i> , 2020 , 67, 3978-3982	2.9	1
4	Barrier Height Stability and Reverse Leakage Mechanisms in Ni/Ga ₂ O ₃ (001) Schottky Barrier Diodes 2019 ,		1

3	Distributed polarization-doped GaN pB diodes with near-unity ideality factor and avalanche breakdown voltage of 1.25 kV. <i>Applied Physics Letters</i> , 2022 , 120, 122111	3.4	0
2	Photoelectric Generation Coefficient of B-Gallium Oxide during Exposure to High-Energy Ionizing Radiation. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2100700	1.6	
1	Field-Effect Transistors 5. <i>Springer Series in Materials Science</i> , 2020 , 639-660	0.9	